

In re Appln. of Tomonori AOYAMA  
Application No. Unassigned

*ABSTRACT AMENDMENTS*

Replace the Abstract with:

A semiconductor device ~~comprises~~ includes a first insulating film on a silicon substrate and a second insulating film on the first insulating film. The first insulating film is a silicon oxide film having a ~~film~~ thickness of 1 nm or less and a suboxide content of 30% or less. The second insulating film is a high dielectric constant insulating film.